



USC120R030B

Power MOSFET

50A, 1200V N-CHANNEL SILICON CARBIDE PLANAR ENHANCEMENT POWER MOSFET

DESCRIPTION

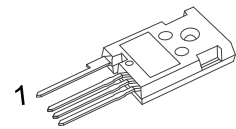
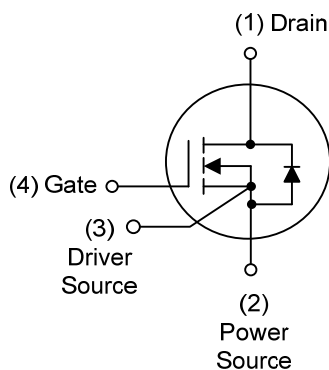
SiC The material can achieve high voltage with most carrier devices (MOSFET) with fast device structure characteristics, so it can realize the three characteristics of "high voltage", "low on resistance" and "high frequency" at the same time.

It is widely used in electric vehicle charger, industrial equipment power supply, efficient power regulator inverter and rectification part and other uses.

FEATURES

- * $R_{DS(ON)} \leq 40 \text{ m}\Omega @ V_{GS}=18\text{V}, I_D=40\text{A}$
- * High Blocking Voltage
- * High Frequency Operation
- * Low on-resistance
- * Fast intrinsic diode with low reverse recovery
- * 100% avalanche tested

SYMBOL



TO-247-4

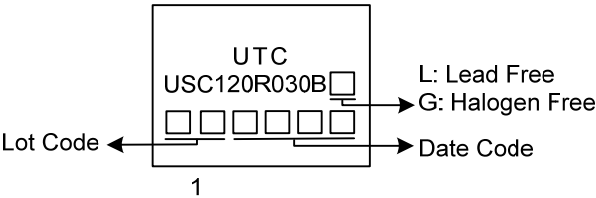
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment				Packing
Lead Free	Halogen Free		1	2	3	4	
USC120R030BL-T474-T	USC120R030BG-T474-T	TO-247-4	D	S	S	G	Tube

Note: Pin Assignment: D: Drain S: Source G: Gate

USC120R030BG-T474-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) T474: TO-247-4 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V _{DSS}	1200	V
Gate-Source Voltage	Dynamic T _{surge} <100nS		V _{GSS}	-10 / +23	V
	Static			-4 / +18	V
Drain Current	Continuous	V _{GS} =18V T _C =25°C	I _D	64	A
		V _{GS} =18V T _C =100°C		45	A
	Pulsed (Note 2)		I _{DM}	170	A
Power Dissipation			P _D	272	W
Junction Temperature			T _J	-55 ~ +175	°C
Storage Temperature			T _{STG}	-55 ~ +175	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

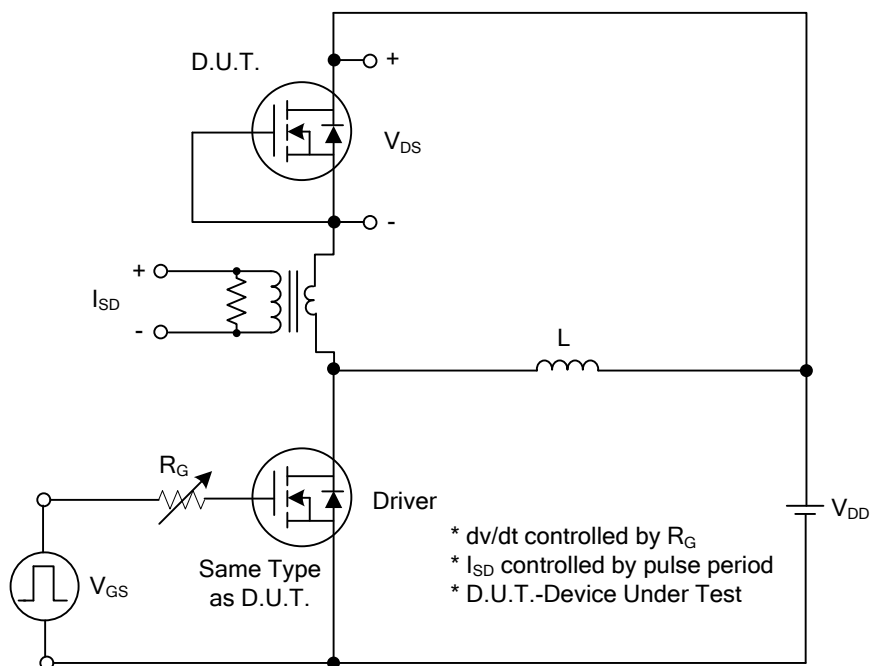
■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	40	°C/W
Junction to Case	θ _{JC}	0.71	°C/W

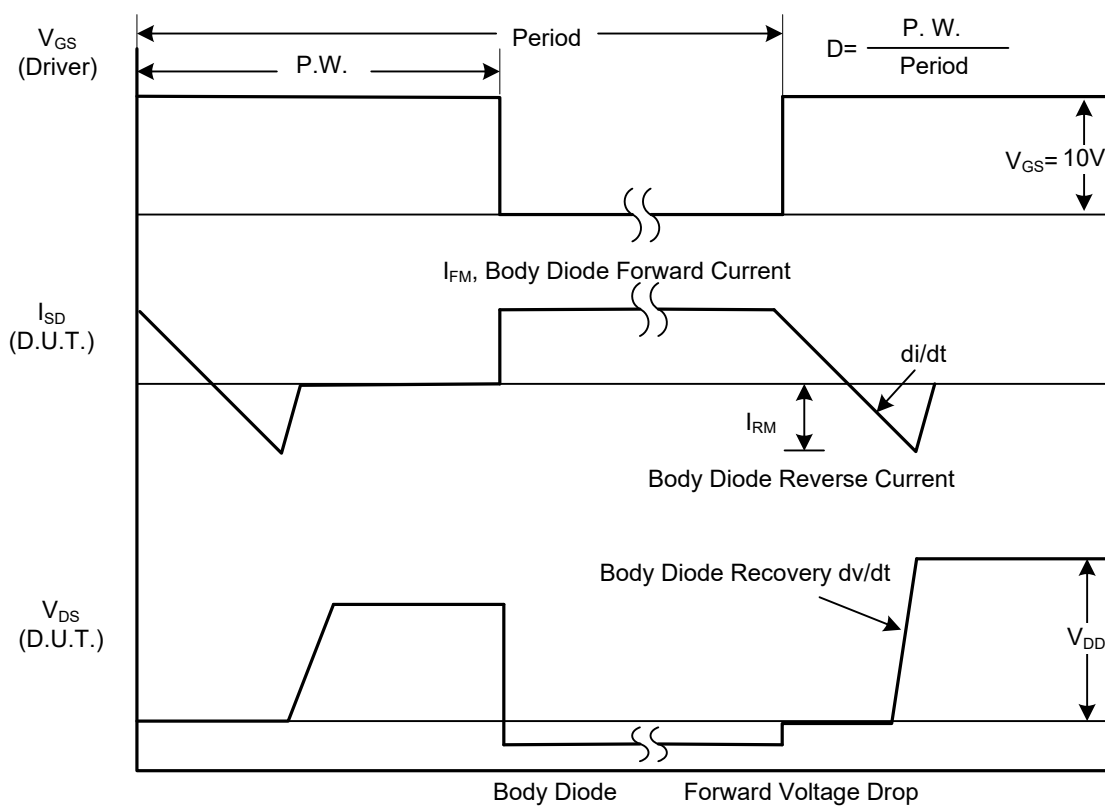
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =100μA, V _{GS} =0V	1200			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =1200V, V _{GS} =0V	0	1	50	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+18V, V _{DS} =0V	0	1	200	nA
	Reverse		V _{GS} =-4V, V _{DS} =0V	-200	-1	0	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =13.5mA	2.0	2.8	3.7	V	
		V _{DS} =V _{GS} , I _D =13.5mA, T _J =150°C		2.0		V	
		V _{DS} =V _{GS} , I _D =13.5mA, T _J =175°C		1.9		V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =18V, I _D =40A		30	40	mΩ	
		V _{GS} =18V, I _D =40A, T _J =150°C		49		mΩ	
		V _{GS} =18V, I _D =40A, T _J =175°C		54		mΩ	
Transconductance	g _{FS}	V _{GS} =20V, I _D =40A		30		S	
		V _{GS} =20V, I _D =40A, T _J =150°C		27		S	
		V _{GS} =20V, I _D =40A, T _J =175°C		26		S	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	V _{DS} =1000V, V _{GS} =0V, f=1MHz		2570		pF	
Output Capacitance	C _{OSS}			106		pF	
Reverse Transfer Capacitance	C _{RSS}			9		pF	
C _{OSS} Stored Energy	E _{OSS}			64		μJ	
SWITCHING PARAMETERS							
Total Gate Charge	Q _G	V _{DS} =800V, V _{GS} =-4V / 18V, I _D =40A		117		nC	
Gate to Source Charge	Q _{GS}			33		nC	
Gate to Drain Charge	Q _{GD}			44		nC	
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =800V, V _{GS} =-4V / 18V, I _D =40A, R _G =2.0Ω, L=100μH		14		ns	
Rise Time	t _R			13		ns	
Turn-OFF Delay Time	t _{D(OFF)}			27		ns	
Fall-Time	t _F			7		ns	
Turn-on switching energy	E _{ON}			310		μJ	
Turn-off switching energy	E _{OFF}			30		μJ	
Internal Gate Resistance	R _{G(int)}	I _D =0A, f=1MHz		1.1		Ω	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Continuous Diode Forward Current	I _S	V _{GS} =-4.0V			50	A	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =-4.0V, I _{SD} =20A		4.1		V	
		V _{GS} =-4.0V, I _{SD} =20A, T _J =150°C		3.7		V	
		V _{GS} =-4.0V, I _{SD} =20A, T _J =175°C		3.6		V	
Body Diode Reverse Recovery Time	t _{rr}	V _{GS} =-4V, I _{SD} =40A, V _R =800V, dI _F /dt=4200A/μs		15		ns	
Body Diode Reverse Recovery Charge	Q _{rr}			210		nC	
Peak Reverse Recovery Current	I _{RRM}			26		A	

■ TEST CIRCUITS AND WAVEFORMS

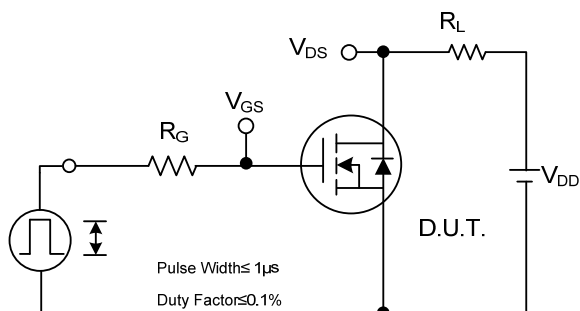


Peak Diode Recovery dv/dt Test Circuit

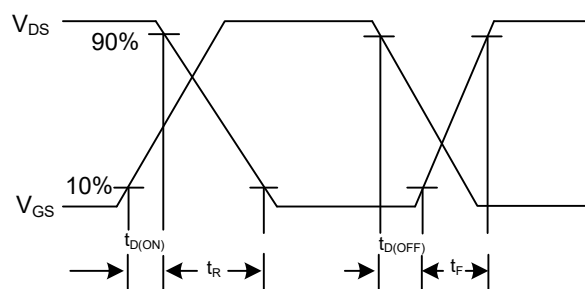


Peak Diode Recovery dv/dt Waveforms

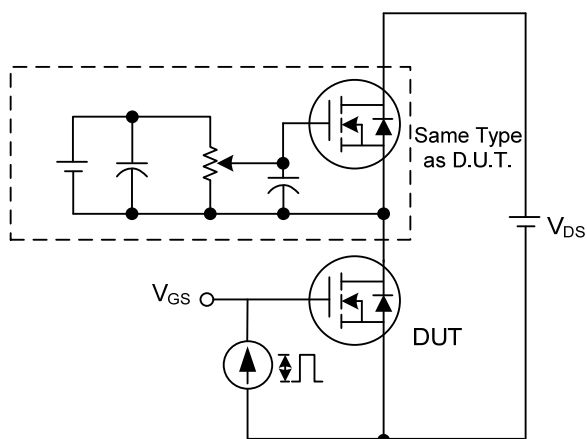
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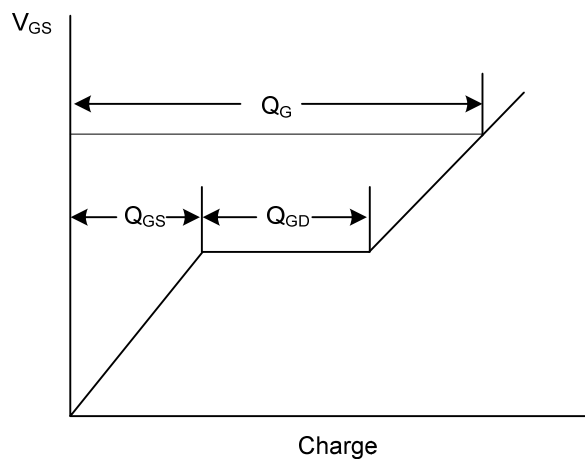
Switching Test Circuit



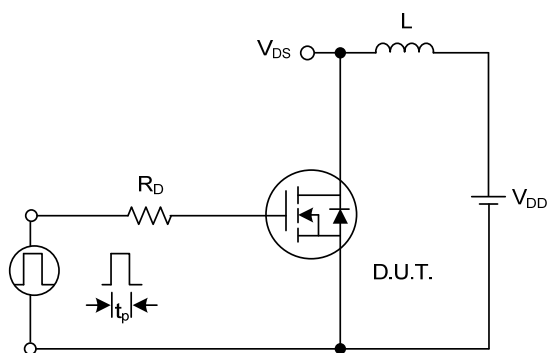
Switching Waveforms



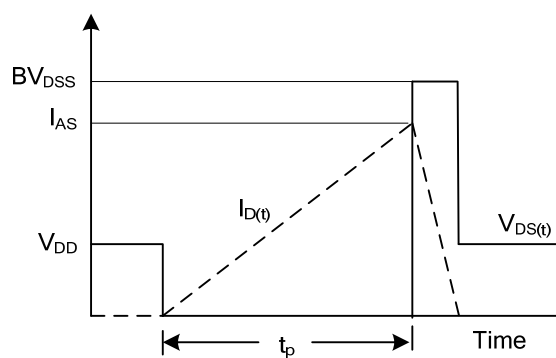
Gate Charge Test Circuit



Gate Charge Waveform

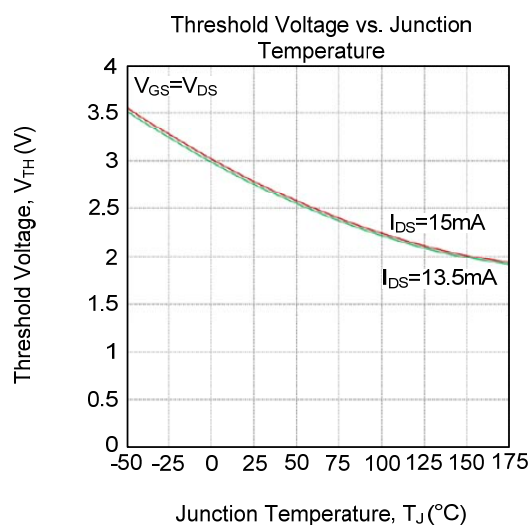
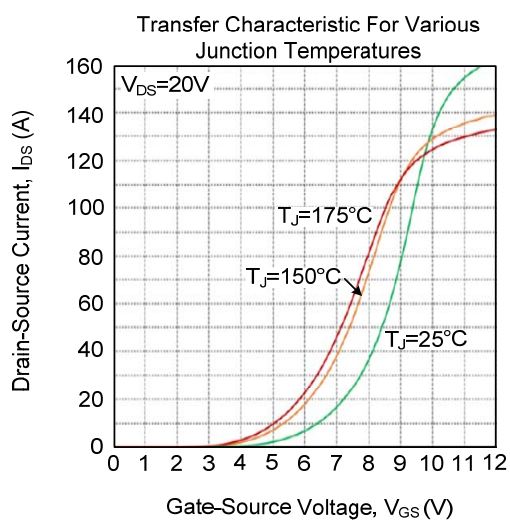
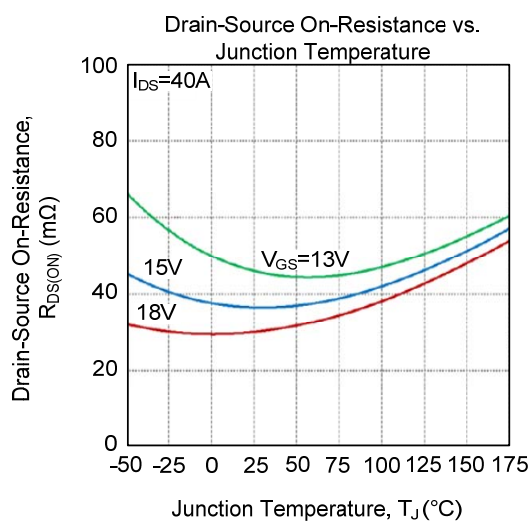
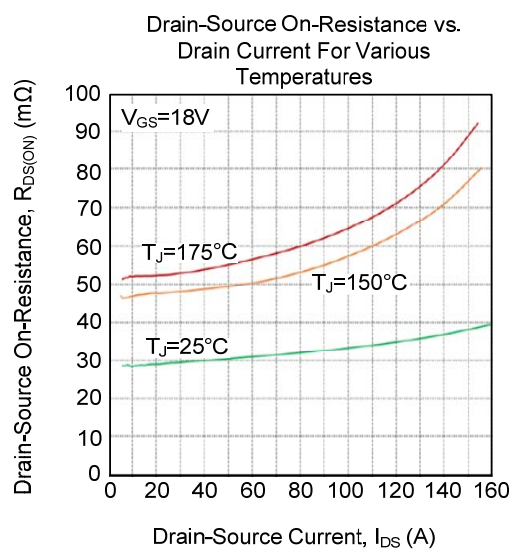
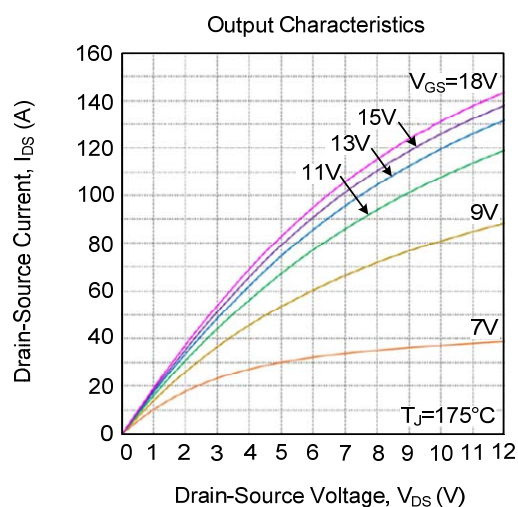
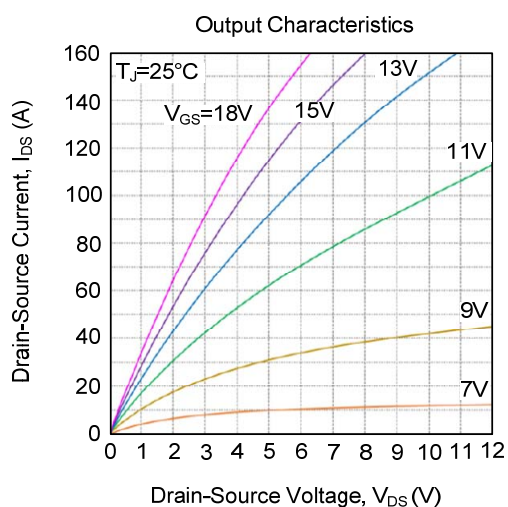


Unclamped Inductive Switching Test Circuit

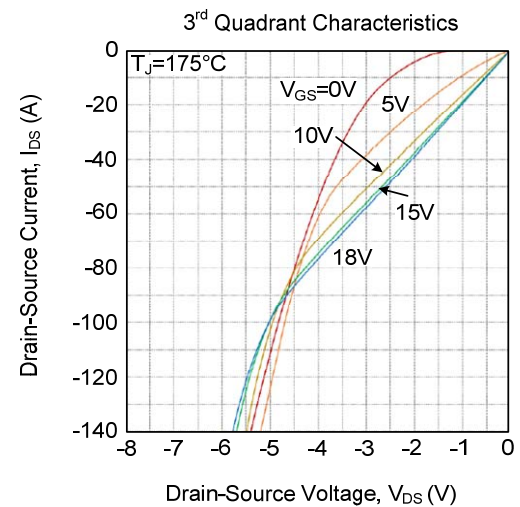
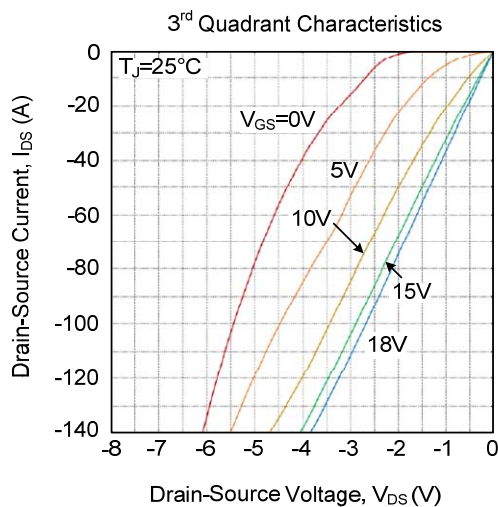
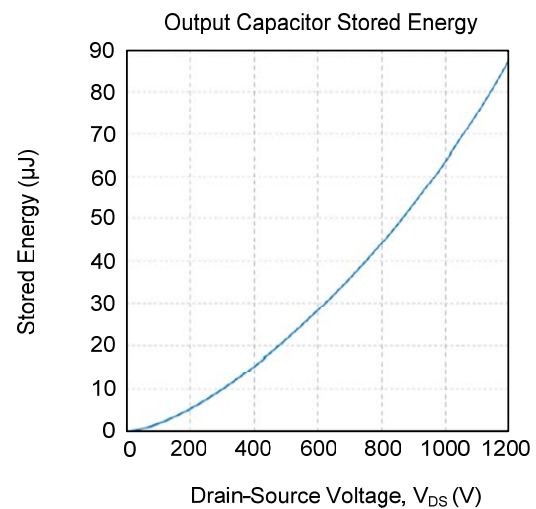
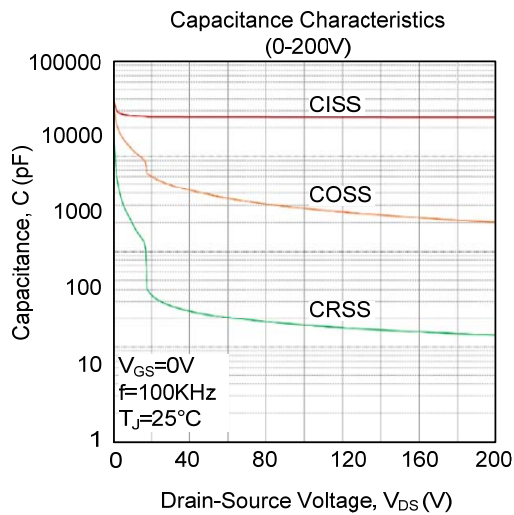
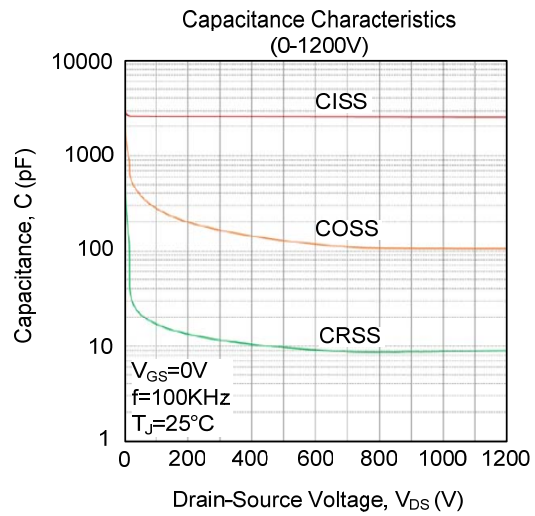
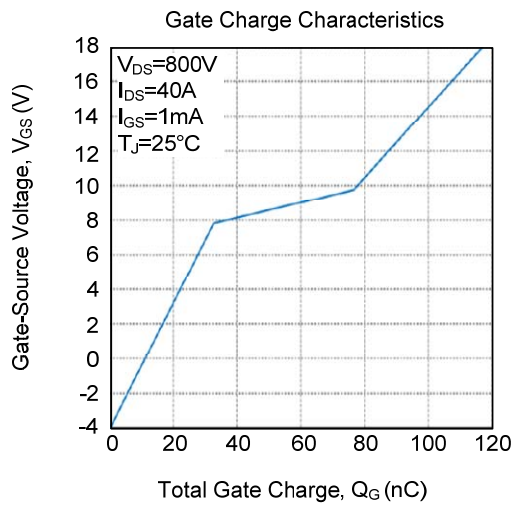


Unclamped Inductive Switching Waveforms

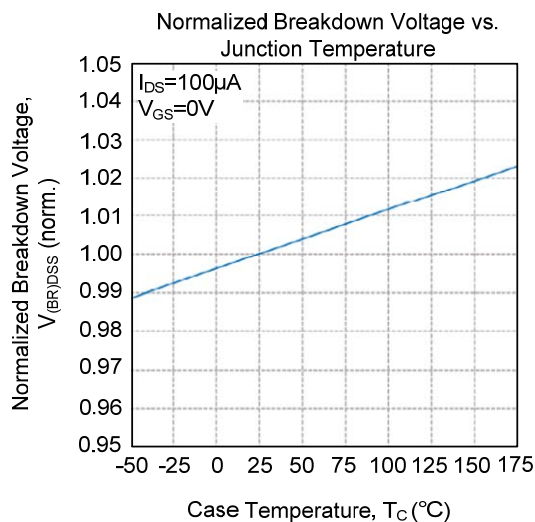
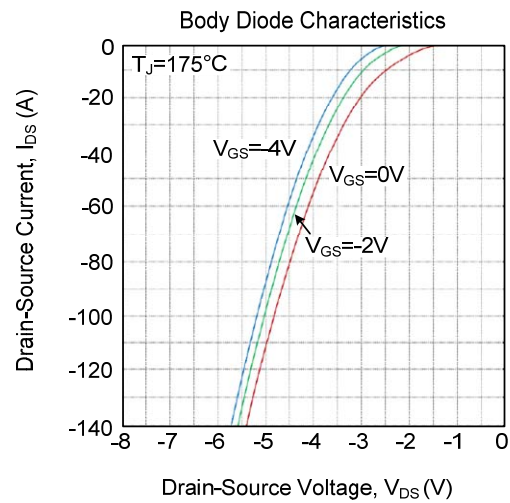
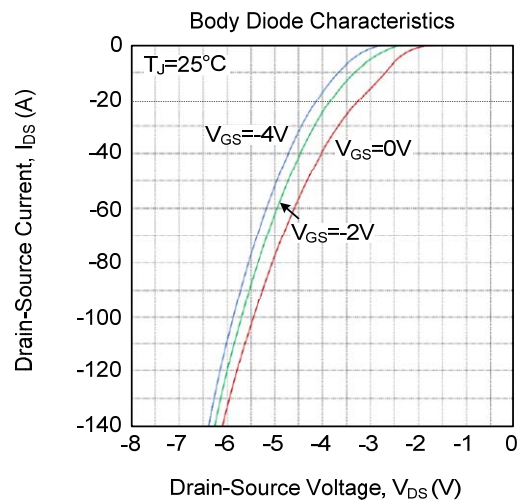
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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